

## SPR220-7.0 Profiles using Contact Aligner

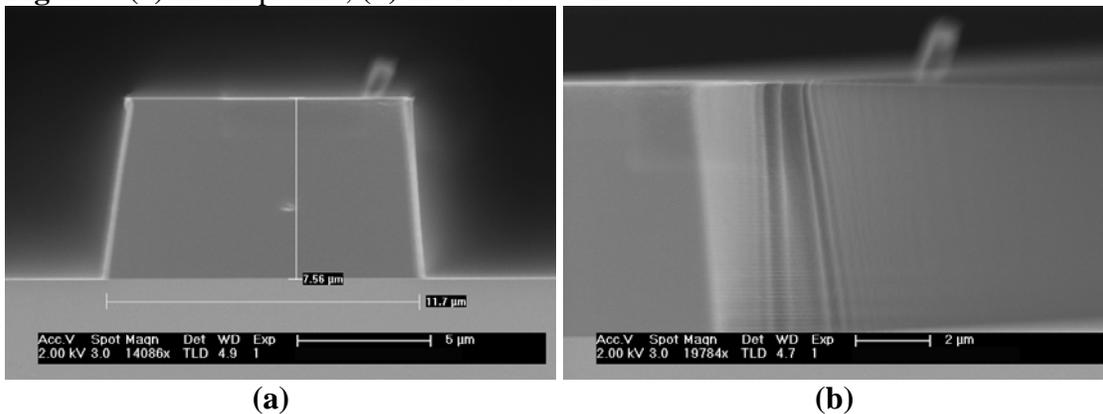
### 2) SPR220-7.0 (Positive Tone)

#### Process:

- Clean a Si wafer piece: Acetone (2') + Methanol (1') in ultrasonic cleaner; DI water resin and N<sub>2</sub> blow dry.
- Dehydration bake @ 110 °C for 5 minutes.
- Spin-on HMDS @ 3500 rpm for 30 seconds.
- Spin-on SPR220-7.0 resist @ 3500 rpm for 45 seconds.
- Soft bake @ 115 °C for 120 seconds.
- Resist edge bead removal: exposure time=120 seconds, development time=90 seconds in MF-701 developer.
- Expose resist for 60 seconds without a filter (7.5 mW/cm<sup>2</sup> using 405-nm detector).
- Wait for 5 minutes to let the resist finish the reaction.
- Develop the exposed resist pattern for 70 seconds in MF-701 developer.

#### Result:

Figure 3 (a) Resist profile; (b) Resist side-wall.



Note: Resist Thickness=7.56 μm.